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Fax Cover Sheet

DATE:	July 2, 2003	PAGES:	<u>11 (eleven) w/cover</u>
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Message

DOCKET GS 150

Please see attached: Response After Final Rejection

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Response after Final Rejection
Expedited Handling Requested - GAU 2826

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Response
110
Patent
10/010,484

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant: Hshieh et al.
Serial No.: 10/010,484
Filed: November 20, 2001
Title: Trench MOSFET Device with Polycrystalline Silicon Source Contact Structure
Art Unit: 2826
Examiner: Tan N. Tran
Docket No.: GS 150

Commissioner for Patents
PO Box 1450
Alexandria, VA 22313-1450

RESPONSE AFTER FINAL REJECTION

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Sir:

In response to the final Office Action dated May 3, 2003 (Paper No. 10), kindly consider the following remarks. In addition, any deficiencies may be charged to deposit account No. 50-1047.